











ZHCSJ81C-FEBRUARY 2003-REVISED DECEMBER 2018

SN74CB3T3125 四通道 FET 总线开关 2.5V、3.3V 低压总线开关,带可耐受 5V 电压的电平转换器

1 特性

- 输出电压转换跟踪 Vcc
- 所有数据 I/O 端口均支持混合模式信号运行
 - 5V 输入降至 3.3V 输出电平位移, V_{CC} 为 3.3V
 - 5V/3.3V 输入降至 2.5V 输出电平位移, V_{CC} 为 2.5V
- 支持器件加电与断电的 5V 耐压 I/O
- 具有接近零传播延迟的双向数据流
- 低导通状态电阻 (r_{on}) 特性 (r_{on} = 5Ω 典型)
- 低输入/输出电容可减小负载 (C_{io(OFF)} = 4.5pF 典型)
- 数据与控制输入提供下冲钳位二极管
- 低功耗(I_{CC} = 20μA 最大值)
- 2.3V 至 3.6V 的 V_{CC} 工作电压范围
- 数据 I/O 支持 0V 至 5V 信号电平(0.8V、1.2V、 1.5V、1.8V、2.5V、3.3V、5V)
- 控制输入可由 TTL 或 5V/3.3V CMOS 输出驱动
- I_{off} 支持局部断电模式运行
- 闩锁性能超过 250mA, 符合 JESD 17 规范
- 静电放电 (ESD) 性能测试符合 JESD 22 规范
 - 2000V 人体放电模式 (A114-B, II 类)
 - 1000V 充电器件模型 (C101)

2 应用

- 支持数字应用:电平转换、USB接口、总线隔离
- 低功耗便携式设备的理想选择

3 说明

SN74CB3T3125 是一种具备低导通状态电阻 (r_{on}) 的高速 TTL 兼容型 FET 总线开关,可实现最短传播延迟。该器件提供可跟踪 V_{CC} 的电压转换,能够在所有数据 I/O 端口上全面支持混合模式信号运行。

SN74CB3T3125 支持使用 5V TTL, 3.3V

LVTTL, 2.5V CMOS 转换标准以及用户定义转换水平的系统(参阅典型直流电压转换特性)。

SN74CB3T3125 被划分为四个 1 位总线开关,各自具备输出使能(1OE、2OE、3OE、4OE)输入。可以作为四个 1 位总线开关或者一个 4 位总线开关。OE 为低时,相关 1 位总线开关打开,A 端口连接至 B 端口,可在两个端口之间实现双向数据流。OE 为高时,相关 1 位总线开关关闭,A、B 端口存在高阻抗状态。

该器件完全 适用于 使用 I_{off} 的局部断电应用。I_{off} 特性确保在关断时防止损坏电流通过器件回流。该器件可在关断时提供隔离。

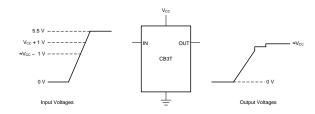
为了确保加电或断电期间的高阻抗状态,**OE** 应通过一个上拉电阻器被连接至 V_{CC}; 该电阻器的最小值由驱动器的电流吸入能力来决定。

器件信息(1)

器件型号	封装	封装尺寸(标称值)	
	VQFN – RGY (14)	3.50mm x 3.50mm	
SN74CB3T3125	TSSOP - PW (14)	5.00mm x 4.40mm	
	TVSOP - DGV (14)	3.60mm x 4.40mm	

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附录。

典型直流电压转换特性



If the input high voltage (V_{IH}) level is greater than or equal to $V_{CC} + 1 V$, and less than or equal to 5.5 V, the output high voltage (V_{OH}) level will be equal to approximately the V_{CC} voltage level.



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4 修订历史记录

注: 之前版本的页码可能与当前版本有所不同。

Changes from Revision B (August 2012) to Revision C

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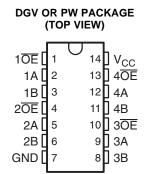
•	添加了应用 列表、器件信息 表、ESD 额定值 表、特性 说明 部分、器件功能模式、应用和实施 部分、电源建议 部分、布局部分、器件和文档支持 部分以及机械、封装和可订购信息 部分
•	删除了订购信息表。
•	Changed t_{en} V_{CC} = 3.3 V MAX value From: 4.4 ns To: 8 ns in the <i>Switching Characteristic</i>

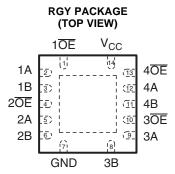
Changes from Revision A (April 2009) to Revision B

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5 Pin Configuration and Functions





Pin Functions

PIN			DECODITION
NAME	NO.	I/O	DESCRIPTION
1 OE	1	I	Active-low enable for switch 1
1A	2	I/O	Switch 1 A terminal
1B	3	I/O	Switch 1 B terminal
2 OE	4	1	Active-low enable for switch 2
2A	5	I/O	Switch 2 A terminal
2B	6	I/O	Switch 2 B terminal
GND	7	-	Ground
ЗА	8	I/O	Switch 3 A terminal
3B	9	I/O	Switch 3 B terminal
3 OE	10	I	Active-low enable for switch 3
4A	11	I/O	Switch 4 A terminal
4B	12	I/O	Switch 4 B terminal
4 OE	13	I	Active-low enable for switch 4
V _{CC}	14	-	Supply voltage pin



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range (2)		-0.5	7	V
V_{IN}	Control input voltage range ⁽²⁾ (3)		-0.5	7	V
$V_{I/O}$	Switch I/O voltage range ^{(2) (3) (4)}	(3) (4)		7	V
I _{IK}	Control input clamp current	V _{IN} < 0		-50	mA
$I_{I/OK}$	I/O port clamp current	V _{I/O} < 0		-50	mA
$I_{I/O}$	ON-state switch current (5)			±128	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to ground unless otherwise specified.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process..

6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	5.5	\/
V _{IH}	High-level control input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2	5.5	V	
.,	V_{CC} = 2.3 V to 2.7 V	0	0.7		
V_{IL}	Low-level control input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0	0.8	V
V _{I/O}	Data input/output voltage		0	5.5	V
T _A	Operating free-air temperature		-40	85	°C

⁽¹⁾ All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	VQFN (RGY)	TSSOP (PW)	TVSOP (DGV)	UNIT
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	55.5	123.3	154.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.9	53.0	64.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	30.9	66.3	88.4	°C/W
ΨЈТ	Junction-to-top characterization parameter	3.6	9.1	10.8	°C/W
ΨЈВ	Junction-to-board characterization parameter	30.9	65.7	87.4	°C/W
R ₀ JC(bot)	Junction-to-case (bottom) thermal resistance	14.6	-	-	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

⁽³⁾ The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽⁴⁾ V_I and V_O are used to denote specific conditions for $V_{I/O}$.

⁵⁾ I_I and I_O are used to denote specific conditions for $I_{I/O}$.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics⁽¹⁾

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITION	MIN TYP ⁽²⁾	MAX	UNIT	
V _{IK}		V _{CC} = 3 V, I _I = -18 mA			-1.2	V
V _{OH}		See Figure 3 through Figure 5				
I _{IN}	Control inputs	V _{CC} = 3.6 V, V _{IN} = 3.6 V to 5.5 V or GND			±10	μΑ
			$V_{I} = V_{CC} - 0.7 \text{ V to } 5.5 \text{ V}$		±20	
I _I		$V_{CC} = 3.6 \text{ V}$, Switch ON, $V_{IN} = V_{CC}$ or GND	$V_{I} = 0.7 \text{ V to } V_{CC} - 0.7 \text{ V}$		-40	μΑ
			$V_1 = 0 \text{ to } 0.7 \text{ V}$		±5	
I _{OZ} (3)	$V_{CC} = 3.6 \text{ V}, V_{O} = 0 \text{ to } 5.5 \text{ V}, V_{I} = 0$, Switch OFF, $V_{IN} = V_{CC}$ or GND		FF, V _{IN} = V _{CC} or GND		±10	μΑ
l _{off}		$V_{CC} = 0$, $V_O = 0$ to 5.5 V, $V_I = 0$			10	μΑ
Icc		$V_{CC} = 3.6 \text{ V}, I_{I/O} = 0$, Switch ON or OFF,	$V_I = V_{CC}$ or GND		20	
		V _{IN} = V _{CC} or GND	V _I = 5.5 V		20	μА
Δl _{CC} ⁽⁴⁾	Control inputs	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V,	Other inputs at V _{CC} or GND		300	μΑ
C _{in}	Control inputs	$V_{CC} = 3.3 \text{ V}, V_{IN} = V_{CC} \text{ or GND}$		3		pF
C _{io(OFF)}		$V_{CC} = 3.3 \text{ V}, V_{I/O} = 5.5 \text{ V}, 3.3 \text{ V}, \text{ or GND, Swith}$	tch OFF, V _{IN} = V _{CC} or GND	4.5		pF
		V 00V 0 11 0V V V 00	$V_{I/O} = 5.5 \text{ V or } 3.3 \text{ V}$	4		
$C_{io(ON)}$		$V_{CC} = 3.3 \text{ V}$, Switch ON, $V_{IN} = V_{CC}$ or GND	V _{I/O} = GND	10		pF
(5)			I _O = 24 mA	5	8	
		$V_{CC} = 2.3 \text{ V}, \text{ TYP at } V_{CC} = 2.5 \text{ V}, V_{I} = 0$	I _O = 16 mA	5	8	
r _{on} ⁽⁵⁾			I _O = 64 mA	5	7	Ω
		$V_{CC} = 3 \text{ V}, V_{I} = 0$	I _O = 32 mA	5	7	

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT	
	(INPUT)	(001F01)	MIN	MAX	MIN	MAX		
t _{pd} ⁽¹⁾	A or B	B or A		0.15		0.25	ns	
t _{en}	ŌĒ	A or B	1	8.5	1	8	ns	
t _{dis}	ŌĒ	A or B	1	9	1	9	ns	

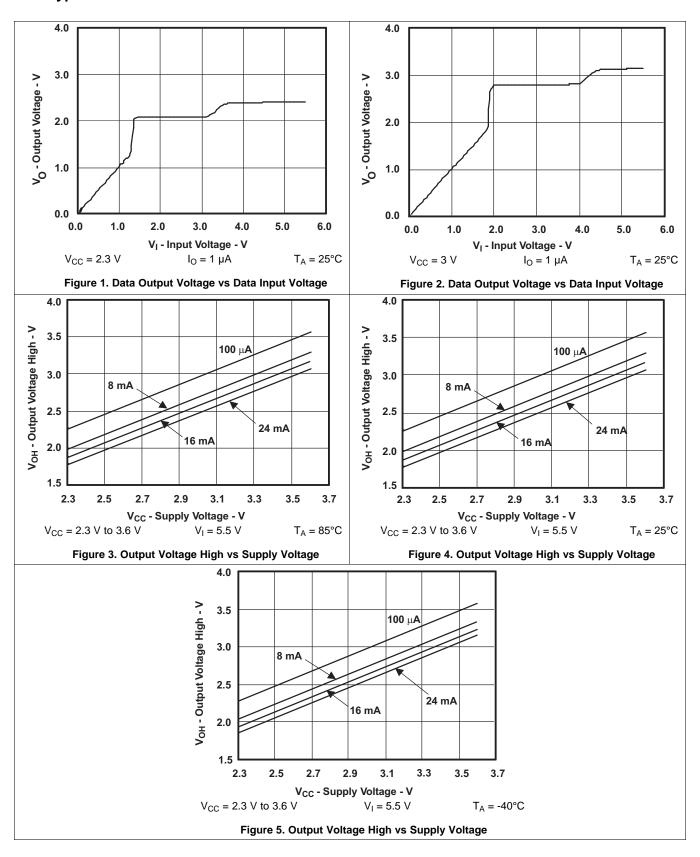
The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

 V_{IN} and I_{IN} refer to control inputs. V_I , V_O , I_I , and I_O refer to data pins. All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C. For I/O ports, the parameter I_{OZ} includes the input leakage current. This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

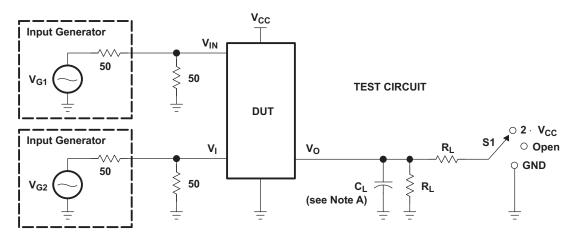


6.7 Typical Characteristics

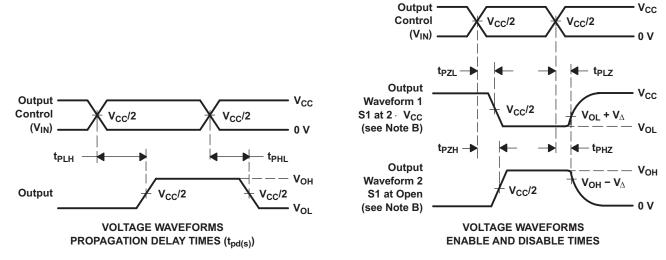




7 Parameter Measurement Information



TEST	V _{CC}	S1	R _L	V _I	CL	V
t _{pd(s)}	2.5 V \pm 0.2 V	Open	500	3.6 V or GND	30 pF	
ρα(5)	3.3 V ± 0.3 V	Open	500	5.5 V or GND	50 pF	
t _{PLZ} /t _{PZL}	2.5 V \pm 0.2 V	2 · V _{CC}	500	GND	30 pF	0.15 V
TPLZ/TPZL	3.3 V \pm 0.3 V	2 · V _{CC}	500	GND	50 pF	0.3 V
t/t	2.5 V ± 0.2 V	Open	500	3.6 V	30 pF	0.15 V
t _{PHZ} /t _{PZH}	3.3 V \pm 0.3 V	Open	500	5.5 V	50 pF	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, $Z_0 = 50 \Omega$, $t_f = 2.5 \text{ ns.}$ the following characteristics: PRR 10 MHz, $Z_0 = 50 \Omega$, $t_f = 2.5 \text{ ns.}$ the following characteristics: PRR 10 MHz, $Z_0 = 50 \Omega$, $Z_0 = 50 \Omega$, Z
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PLH} are the same as t_{d(s)}. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

Figure 6. Test Circuit and Voltage Waveforms



8 Detailed Description

8.1 Overview

The SN74CB3T3215 device is organized as four 1-bit bus switches with separate ouput-enable (10E, 20E, 30E, and 4 OE) inputs. When OE is low, the associated 1-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 1-bit bus switch is OFF, and a high-impedance state exists between the A and B ports. This device is fully specified for partial-power-down applications using loff. The loff feature ensures that damaging current will not backflow through the device when it is powered down. The SN74CB3T3125 device has isolation during power off. To ensure the high-impedance state during power up or power down, OE should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram

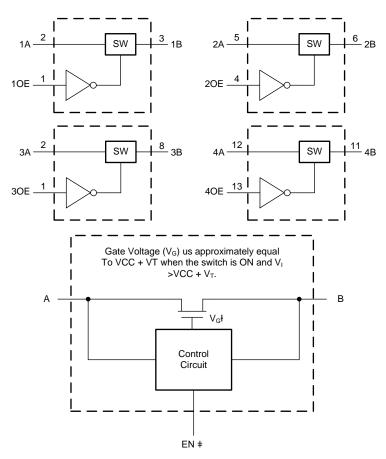


Figure 7. Simplified Schematic, Each FET Switch (SW)



8.3 Feature Description

The SN74CB3T3125 is ideal for low-power portable equipment. Power consumption is low by design, $I_{CC}=20~\mu A$, On-state resistance is low ($r_{on}=5~\Omega$) It has bidirectional data flow with near zero propagation delay. The devices minimizes loading due to the low input/output capacitance $C_{io(OFF)}=4.5~pF$ Typical. Operating VCC range from 2.3 V to 3.6 V. The output tracks VCC. Data and control inputs provide undershoot clamp diodes. Control inputs can be driven by TTL or 5-V/3.3-V CMOS outputs. It supports mixed-mode signal operation on all data I/O ports. Data I/Os support 0- to 5-V signaling levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V). The device is protected from damaging current, loff supports partial shutdown which prevents the current from flowing back through the device when it is powered down. In addition, it has 5-V tolerant I/Os with device powered up or powered down. The device is latch-up resistant with 250 mA exceeding the JESD 17 standard, providing protection from destruction due to latch-up. This device is protected against electrostatic discharge. It is tested per JESD 22 using 2000-V Human-Body Model (A114-B, Class II), and 1000-V Charged-Device Model (C101).

8.4 Device Functional Modes

Table 1 lists the functional modes for the SN74CB3T3125.

Table 1. Function Table (Each Bus Switch)

INPUT OE	INPUT/OUTPUT A	FUNCTION
L	В	A port = B port
Н	Z	Disconnect

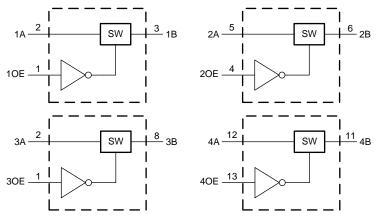


Figure 8. Logic Diagram (Positive Logic)



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

This application is specifically to connect a 5-V bus to a 3.3 V device. Ideally, set VCC to 3.3 V. It is assumed that communication in this particular application is one-directional, going from the bus controller to the device.

9.2 Typical Application

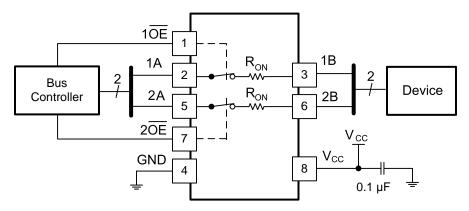


Figure 9. Application Circuit

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. Because this design is for down-translating voltage, no pull-up resistors are required.

9.2.2 Detailed Design Procedure

- 1. Recommended Input conditions Specified high and low levels. See (V_{IH} and V_{IL}) in *Recommended Operating Conditions* Inputs are overvoltage tolerant allowing them to go as high as 7 V at any valid VCC.
- 2. Recommend output conditions Load currents should not exceed 128 mA on each channel.



Typical Application (continued)

9.2.3 Application Curves

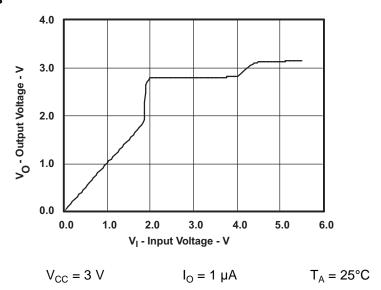


Figure 10. Data Output Voltage vs Data Input Voltage

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions.

Each VCC terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If there are multiple pins labeled VCC, then a 0.01- μ F or 0.022- μ F capacitor is recommended for each VCC because the VCC pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example VCC and VDD, a 0.1- μ F bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.



11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 11 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

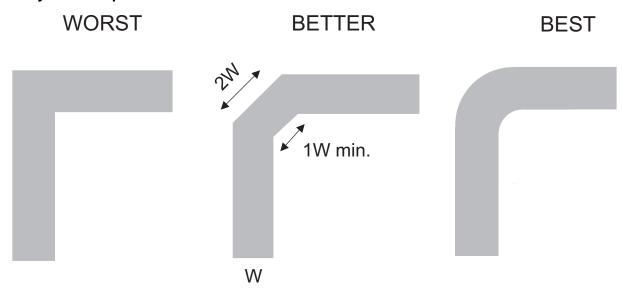


Figure 11. Example Layout

www.ti.com.cn

12 器件和文档支持

12.1 器件支持

12.2 接收文档更新通知

要接收文档更新通知,请导航至 Tl.com.cn 上的器件产品文件夹。单击右上角的*通知我*进行注册,即可每周接收产 品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范, 并且不一定反映 TI 的观点;请参阅 TI 的 《使用条款》。

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12.4 商标

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All other trademarks are the property of their respective owners.

12.5 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序,可 能会损坏集成电路。

▲ SSD 的损坏小至导致微小的性能降级,大至整个器件故障。 精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可 能会导致器件与其发布的规格不相符。

12.6 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且 不会对此文档进行修订。如需获取此数据表的浏览器版本,请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74CB3T3125DGVR	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVR.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVRG4	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125DGVRG4.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125PW	Obsolete	Production	TSSOP (PW) 14	-	-	Call TI	Call TI	-40 to 85	KS125
SN74CB3T3125PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125PWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125
SN74CB3T3125RGYR	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	KS125
SN74CB3T3125RGYR.B	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	KS125

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

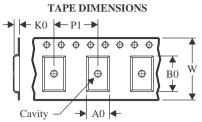
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3T3125DGVRG4	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3T3125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3125RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CB3T3125DGVRG4	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CB3T3125PWR	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74CB3T3125RGYR	VQFN	RGY	14	3000	353.0	353.0	32.0

DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

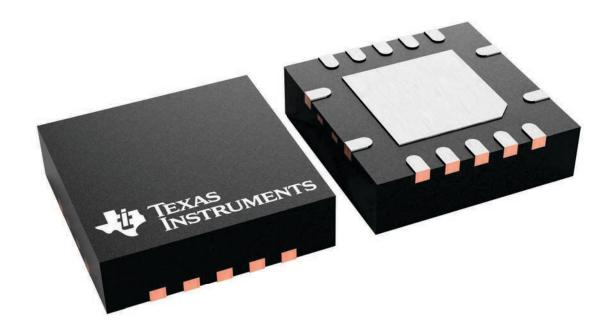
- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



3.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

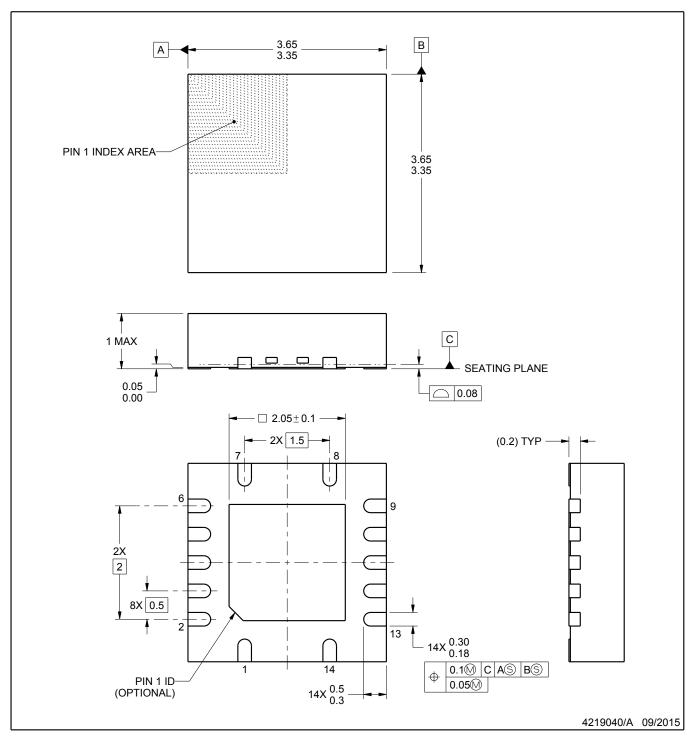
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



INSTRUMENTS www.ti.com



PLASTIC QUAD FLATPACK - NO LEAD

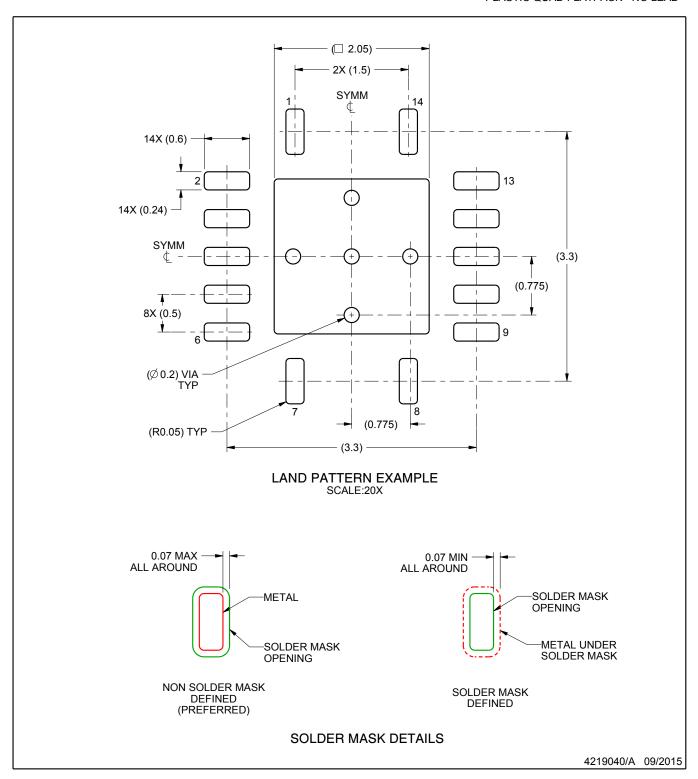


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
 The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

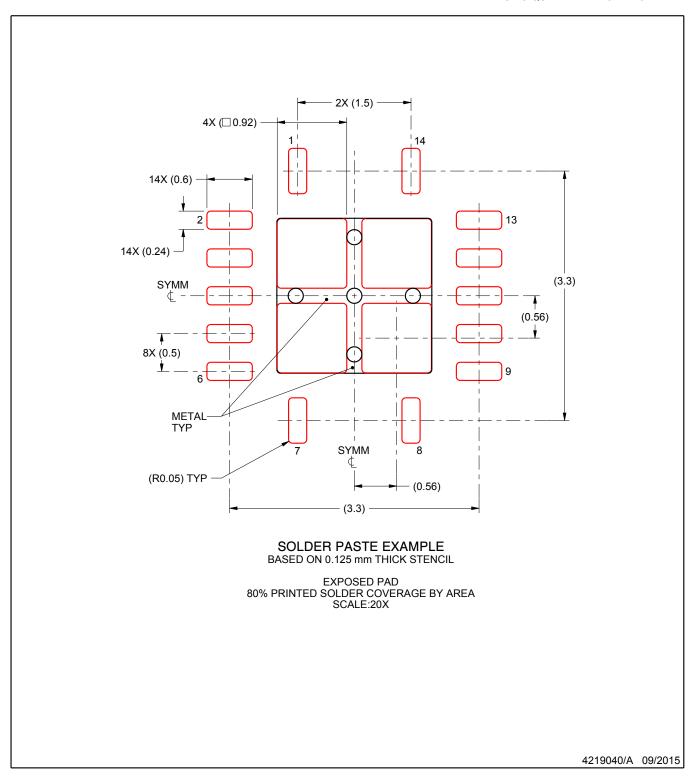


NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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